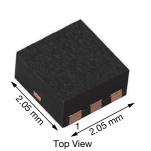


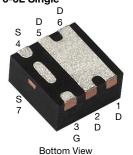
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Vishay Siliconix

Automotive P-Channel 20 V (D-S) 175 °C MOSFET

PowerPAK® SC-70-6L Single





Marking Code: QGXXXX

PRODUCT SUMMARY								
V _{DS} (V)	-20							
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.113							
$R_{DS(on)}(\Omega)$ at $V_{GS} = -2.5 \text{ V}$	0.200							
I _D (A)	-2.68							
Configuration	Single							
Package	PowerPAK SC-70							

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified ^d
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





	(1, 2, 5, 6) D
(3) G O —	
P-Channel MOSFET	(4) S

PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage		V_{DS}	-20	V		
Gate-source voltage		V_{GS}	± 8	¬		
Continuous drain current	T _C = 25 °C		-2.68			
Continuous drain current	T _C = 125 °C	I _D	-1.55			
Continuous source current (diode conduct	tion) ^a	I _S	3.75	Α		
Pulsed drain current ^b		I _{DM}	10			
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-7			
Single pulse avalanche energy	L = U. I IIIH	E _{AS}	2.45	mJ		
M. t. b. c. b	T _C = 25 °C	Б	13.6	W		
Maximum power dissipation ^b	T _C = 125 °C	P_{D}	4.5			
Operating junction and storage temperatu	T _J , T _{stg}	-55 to +175	°C			

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	LIMIT	UNIT					
Junction-to-ambient	PCB mount c	R _{thJA}	90	°C/W					
Junction-to-case (drain)		R _{thJF}	11	C/VV					

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. Parametric verification ongoing



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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static	-	•				l .		
Drain-source breakdown voltage	V _{DS}	V _{GS}	$V_{GS} = 0$, $I_D = -250 \mu A$		-	-	.,	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 μA	-0.6	-1.0	-1.5	V	
Cata aguraa laakaga		V _{DS} =	-	-	± 100	nA		
Gate-source leakage	I _{GSS}	V _{DS} =	= 0 V, V _{GS} = ± 8 V	-	-	± 5		
		$V_{GS} = 0 V$	V _{DS} = -20 V	-	-	-1	μA	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -20 V, T _J = 125 °C	-	-	-50		
		V _{GS} = 0 V	V _{DS} = -20 V, T _J = 175 °C	V, T _J = 175 °C				
On-state drain current a	I _{D(on)}	$V_{GS} = -4.5 \text{ V}$	$V_{DS} \ge 5 V$	-8	-	-	Α	
		V _{GS} = -4.5 V	I _D = -2 A	-	0.093	0.113		
Duning and an add and an all and a	Б	V _{GS} = -4.5 V	I _D = -2 A, T _J = 125 °C	-	-	0.161		
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = -4.5 V	I _D = -2 A, T _J = 175 °C	-	-	0.184	Ω	
		V _{GS} = -2.5 V	I _D = -2 A	-	0.165	0.200		
Forward transconductance b	9 _{fs}	V _{DS} :	-	4.7	-	S		
Dynamic ^b								
Input capacitance	C _{iss}			-	298	375		
Output capacitance	C _{oss} V _{GS} =		$V_{DS} = -10 \text{ V, f} = 1 \text{ MHz}$	-	104	130	pF	
Reverse transfer capacitance	C _{rss}				56	70		
Total gate charge ^c	Q_g				4.2	5.3		
Gate-source charge c	Q_{gs}	$V_{GS} = -4.5 \text{ V}$	$V_{GS} = -4.5 \text{ V}$ $V_{DS} = -10 \text{ V}, I_{D} = -2.4 \text{ A}$		0.75	-	nC	
Gate-drain charge c	Q _{gd}				1.2	-		
Gate resistance	R_g	f = 1 MHz		5.1	8.6	14	Ω	
Turn-on delay time ^c	t _{d(on)}			-	9	11.1		
Rise time ^c	t _r	$V_{DD} =$	-	17	21.4	ns		
Turn-off delay time ^c	t _{d(off)}	I _D ≅ -1.9 A,	-	19	24			
Fall time ^c	t _f	7		-	8	10		
Source-Drain Diode Ratings and Char	acteristics	•						
Pulsed current ^a	I _{SM}			-	-	-12.7	Α	
Forward voltage	V_{SD}	I _F :	-	-0.8	-1.2	V		

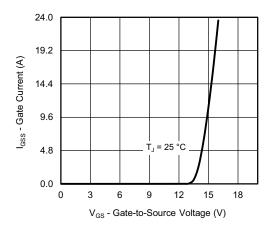
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

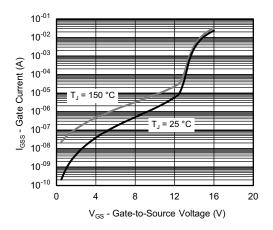
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



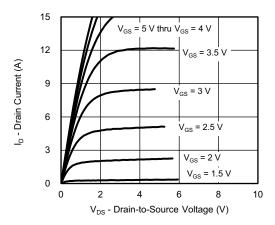
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



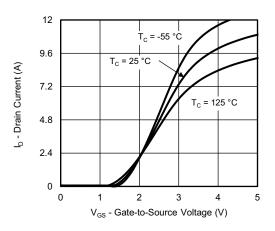
Gate Current vs. Gate-Source Voltage



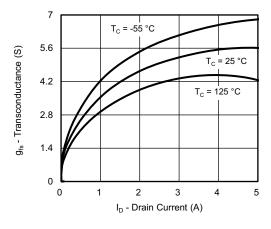
Gate Current vs. Gate-Source Voltage



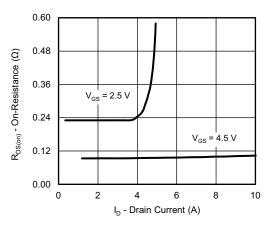
Output Characteristics



Transfer Characteristics



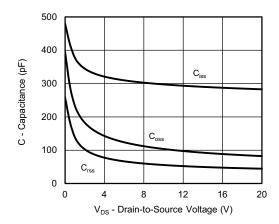
Transconductance



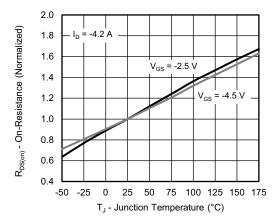
On-Resistance vs. Drain Current



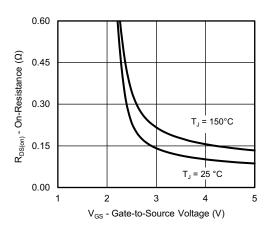
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



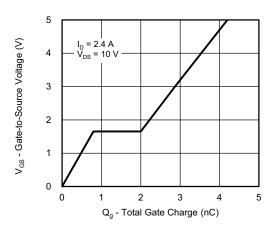
Capacitance



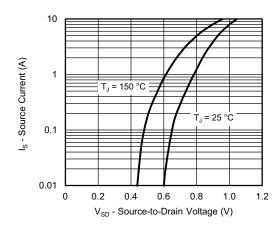
On-Resistance vs. Junction Temperature



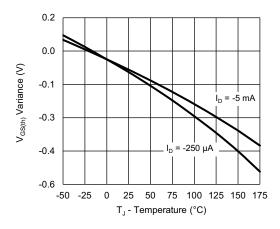
On-Resistance vs. Gate-to-Source Voltage



Gate Charge



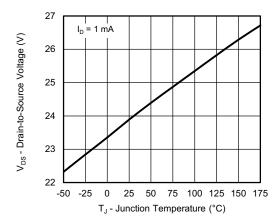
Source-Drain Diode Forward Voltage



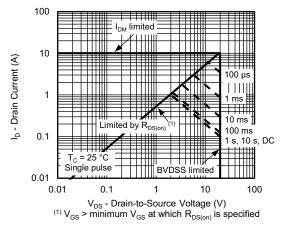
Threshold Voltage



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

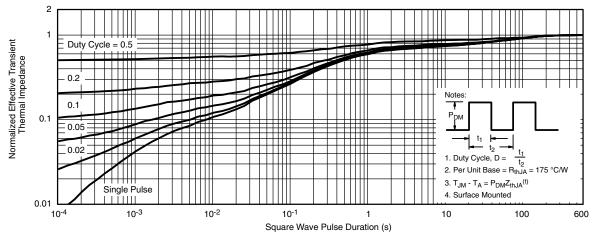


Drain Source Breakdown vs. Junction Temperature



Safe Operating Area

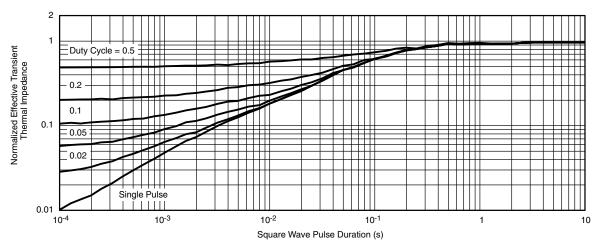
THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

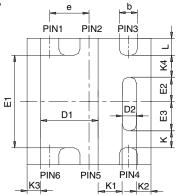
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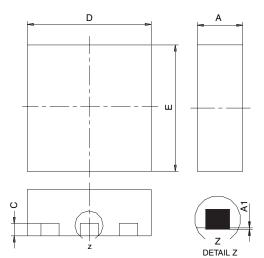
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

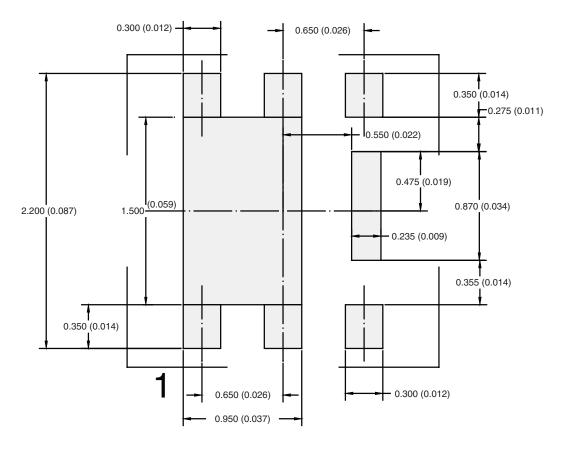
	SINGLE PAD						DUAL PAD						
DIM	M	ILLIMETER	RS	INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC			
K		0.275 TYP	١		0.011 TYP		0.275 TYP			0.011 TYP			
K1		0.400 TYP	١		0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP	١		0.009 TYP			0.252 TYP			0.010 TYP		
К3		0.225 TYP	1	0.009 TYP									
K4		0.355 TYP		0.014 TYP									
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
FCN: C-07431 - Rev. C. 06-Aug-07													

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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